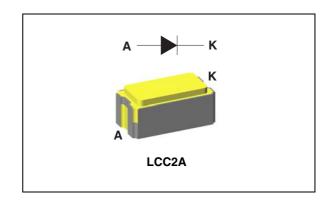


## 1N5806U

## Aerospace 2.5 A fast recovery rectifier

### **Features**

- Aerospace applications
- Surface mount hermetic package
- High thermal conductivity materials
- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop
- Package weight: 0.12 g
- Target radiation qualification
  - 150 krad (Si) low dose rate
  - 3 Mrad (Si) high dose rate
- Under ESCC qualification



## **Description**

This power ultrafast recovery rectifier is designed and packaged to comply with the ESCC5000 specification for aerospace products. It is housed in a surface mount hermetically sealed LCC2A package whose footprint is 100% compatible with industry standard solutions in D5A.

The 1N5806U is suitable for switching mode power supplies and high frequency DC to DC converters such as low voltage high frequency inverter, free wheeling or polarity protection.

Table 1. Device summary<sup>(1)</sup>

Order code	ESCC detailed specification	Quality level	Lead finish	EPPL	I <sub>F(AV)</sub>	V <sub>RRM</sub>	T <sub>j(max)</sub>	V <sub>F (max)</sub>
1N5806UA1	-	Engineering model	Gold plated	-				
1N5806U01A	5101/014/13	Flight part	Gold plated	Υ	2.5 A	150 V	175 °C	1.0 V
1N5806U02A	5101/014/14	Flight part	Solder dip	Υ				

<sup>1.</sup> Contact ST sales office for information about the specific conditions for products in die form and QML-Q versions.

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## 1 Characteristics

Table 2. Absolute ratings (limiting values)

Symbol	Parameter	Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage	150	V	
I <sub>F(RMS)</sub>	Forward rms current		6	Α
I <sub>F(AV)</sub>	Average forward rectified current $T_c = 135  ^{\circ}C,  \delta = 0.5$		2.5	Α
1.	Forward surge current	t <sub>p</sub> = 8.3 ms sinusoidal	35	Α
IFSM	$t_p = 10 \text{ ms sinusoidal}$		33	^
T <sub>stg</sub>	Storage temperature range	-65 to + 175	°C	
T <sub>j</sub>	Maximum operating junction temperature	175	°C	
T <sub>sol</sub>	Maximum soldering temperature (1)	245	°C	

<sup>1.</sup> Maximum duration 5 s. The same package must not be re-soldered until 3 minutes have elapsed.

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
R <sub>th (j-c)</sub>	Junction to case	13	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
	Reverse current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = 150 V	-	-	0.5	
I <sub>R</sub> <sup>(1)</sup>		T <sub>j</sub> = 125 °C	v <sub>R</sub> = 150 v	-	-	20	^
IR ` ′		T <sub>j</sub> = 25 °C	V <sub>R</sub> = 160 V	-	-	10	μΑ
		T <sub>j</sub> = -65 °C		-	-	10	
	Forward voltage	T <sub>j</sub> = 25 °C		-	-	880	
V <sub>F</sub> <sup>(2)</sup>		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 1 A	-	-	800	mV
V <sub>F</sub> `′		T <sub>j</sub> = -65 °C		-	-	1075	IIIV
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 2.5 A	-	-	1000	

<sup>1.</sup> Pulse test:  $tp = 5 \text{ ms}, \delta < 2\%$ 

To evaluate the conduction losses use the following equation:

$$P = 0.70 \times I_{F(AV)} + 0.10 \times I_{F}^{2}(RMS)$$

<sup>2.</sup> Pulse test: tp = 680  $\mu$ s,  $\delta$  < 2%

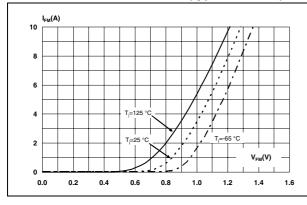
www.DataShat4U60m Characteristics

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>RR</sub>	Reverse recovery time	$I_F = I_R = 0.5 \text{ A}, I_{rr} = 0.05 \text{ A}, dI/dt = -65 \text{ A/}\mu\text{s}$ (min.)	-	-	25	ns
	·	$I_F = 1 \text{ A}, V_R = 30 \text{ V}, dI/dt = -50 \text{ A}/\mu\text{s},$	-	-	30	
V <sub>FP</sub>	Forward recovery voltage	I <sub>FM</sub> = 250 mA	-	-	2.2	٧
t <sub>FR</sub>	Forward recovery time	$I_{FM} = 250 \text{ mA}, V_{RF} = 1.1 \text{ x V}_{F}$	-	-	15	ns
C <sub>j</sub>	Diode capacitance	V <sub>R</sub> = 10 V, F = 1 MHz	-	-	25	pF

Figure 1. Forward voltage drop versus forward current (typical values)

Figure 2. Forward voltage drop versus forward current (maximum values)



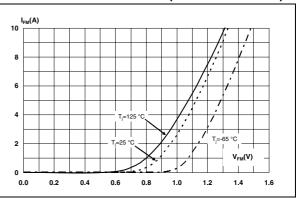
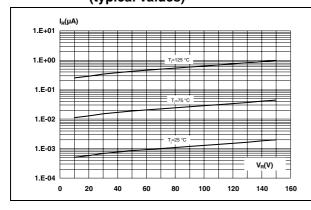
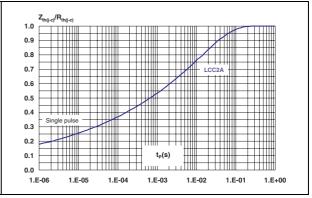


Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

Figure 4. Relative variation of thermal impedance, junction to case, versus pulse duration

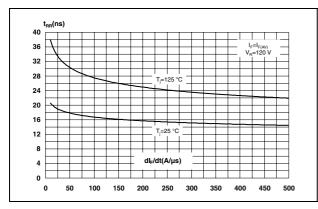


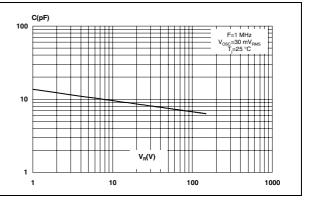


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Figure 5. Reverse recovery time versus dI<sub>F</sub>/dt

Figure 6. Junction capacitance versus reverse voltage applied (typical values)





**577** 

www.DataSh660m **Package information** 

#### **Package information** 2

Table 6.

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK<sup>®</sup> is an ST trademark.

Leadless chip carrier 2 (LCC2A) package dimensions

**Dimensions** Ref. Millimeters

Inches Min. Min. Max. Max. Тур. Typ.  $A^{(1)}$ 1.86 2.03 2.20 0.073 0.080 0.087 0.192 В 4.54 4.67 4.87 0.179 0.184 2.46 С 0.97 0.102 2.33 2.59 0.92 0.074 1.53 1.70 1.87 0.060 0.067 0.019 0.028 Ε 0.48 0.71 F 0.051 1.3 G 2.16 0.085 Н 0.86 00.34 0.15 0.006 0.15 0.006 r1 r2 0.20 0.008

Note 1: The anode is identified by metallization in two top internal angles and the index mark.

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<sup>1.</sup> Measurement prior to solder coating the mounting pads on bottom of package

# 3 Ordering information

Table 7. Ordering information<sup>(1)</sup>

Order code	ESCC detailed specification	Package	Lead finish	Marking	EPPL	Weight	Packing
1N5806UA1	-		Gold plated	06UA1	-	0.12 g	
1N5806U01A	5101/014/13	LCC2A	Gold plated	06U01A	Υ	0.10 a	Waffle pack
1N5806U02A	5101/014/14		Solder dip	06U02A	Υ	0.12 g	Param

Contact ST sales office for information about the specific conditions for products in die form and QML-Q versions

# 4 Revision history

Table 8. Document revision history

Date	Revision	Changes
27-Jul-2009	1	First issue.



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